DISCRETE SEMICONDUCTORS

DATA SHEET

BUJ103AXSilicon Diffused Power Transistor

Product specification

August 1998



Silicon Diffused Power Transistor

BUJ103AX

GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in a plastic full-pack envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

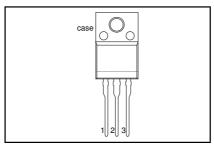
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	700	٧
V_{CBO}	Collector-Base voltage (open emitter)		-	700	V
V _{CEO}	Collector-emitter voltage (open base)		-	400	V
I _C	Collector current (DC)		-	4	Α
1 1	Collector current peak value		-	8	Α
P _{tot}	Total power dissipation	$T_{hs} \le 25 ^{\circ}C$	-	26	W
V _{CEsat}	Collector-emitter saturation voltage	1	0.25	1.0	V
h _{FEsat}	DC current gain	$I_{\rm C} = 3 \text{ A}; V_{\rm CF} = 5 \text{ V}$	12.5	-	
t _f	Fall time	$I_C = 3 \text{ A}; V_{CE} = 5 \text{ V}$ $IC=2A, I_{B1}=0.4A$	33	80	ns

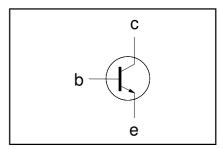
PINNING - SOT186A

PIN	DESCRIPTION	
1	base	
2	collector	
3	emitter	
case	isolated	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CESM}	Collector to emitter voltage	$V_{BE} = 0 \text{ V}$	-	700	٧
V _{CEO}	Collector to emitter voltage (open base)		-	400	V
V _{CBO}	Collector to base voltage (open emitter)		-	700	V
I _C	Collector current (DC)		-	4	Α
I _{CM}	Collector current peak value		-	8	Α
I _B	Base current (DC)		-	2	Α
I _{BM}	Base current peak value		-	4	Α
Ptot	Total power dissipation	T _{hs} ≤ 25 °C	-	26	W
T _{stq}	Storage temperature		-65	150	°C
T _j	Junction temperature		-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS		MAX.	UNIT
R _{th j-hs}	Junction to heatsink	with heatsink compound	-	4.8	K/W
R _{th j-a}	Junction to ambient	in free air	55	=	K/W

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ISOLATION LIMITING VALUE & CHARACTERISTIC

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	ı		2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	рF

STATIC CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
CES CES	Collector cut-off current ¹	$ \begin{vmatrix} V_{\text{BE}} = 0 \text{ V; } V_{\text{CE}} = V_{\text{CESMmax}} \\ V_{\text{BE}} = 0 \text{ V; } V_{\text{CE}} = V_{\text{CESMmax}} \\ T_{j} = 125 \text{ °C} \end{vmatrix} $	-	-	1.0 2.0	mA mA
I _{CBO}	Collector cut-off current ¹	$egin{align*} V_{\text{CBO}} = V_{\text{CESMmax}}(700V) \ V_{\text{CEO}} = V_{\text{CEOMmax}}(400V) \ \end{split}$	- -	- -	0.1 0.1	mA mA
${ m I_{EBO}} { m V_{CEOsust}}$	Emitter cut-off current Collector-emitter sustaining voltage	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}$ $I_{B} = 0 \text{ A}; I_{C} = 10 \text{ mA};$ $I_{C} = 25 \text{ mH}$	- 400	- -	0.1 -	mA V
V _{CEsat} V _{BEsat} h _{FE} h _{FE} h _{FEsat}	Collector-emitter saturation voltage Base-emitter saturation voltage DC current gain DC current gain	$\begin{aligned} & I_{C} = 3.0 \text{ A; } I_{B} = 0.6 \text{ A} \\ & I_{C} = 3.0 \text{ A; } I_{B} = 0.6 \text{ A} \\ & I_{C} = 1 \text{ mA; } V_{CE} = 5 \text{ V} \\ & I_{C} = 0.5 \text{ A; } V_{CE} = 5 \text{ V} \\ & I_{C} = 2 \text{ A; } V_{CE} = 5 \text{ V} \\ & I_{C} = 3 \text{ A; } V_{CE} = 5 \text{ V} \end{aligned}$	- 10 12 13.5	0.25 0.97 17 20 16 12.5	1.0 1.5 32 32 20	V

DYNAMIC CHARACTERISTICS

 T_{hs} = 25 °C unless otherwise specified

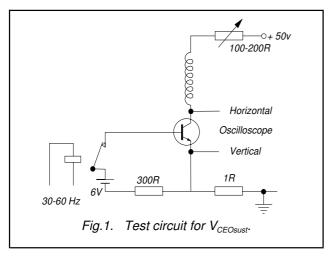
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	$I_{Con} = 2.5 \text{ A}; I_{Bon} = -I_{Boff} = 0.5 \text{ A}; R_L = 75 \text{ ohms}; V_{BB2} = 4 \text{ V};$			
t _{on}	Turn-on time		0.52	0.6	μs
t _s	Turn-off storage time		2.7	3.2	μs
L _f	Turn-off fall time		0.3	0.43	μs
	Switching times (inductive load)	$I_{Con} = 2 \text{ A}; I_{Bon} = 0.4 \text{ A}; L_{B} = 1 \mu\text{H}; $ - $V_{RB} = 5 \text{ V}$			
t _s	Turn-off storage time	55	1.2	1.33	μs
t _f	Turn-off fall time		33	80	ns
	Switching times (inductive load)	$I_{Con} = 2 \text{ A}; I_{Bon} = 0.4 \text{ A}; L_{B} = 1 \mu\text{H}; \\ -V_{BB} = 5 \text{ V}; T_{i} = 100 ^{\circ}\text{C}$			
l t _s	Turn-off storage time	BB - , j	-	1.8	μs
t _f	Turn-off fall time		-	200	ns

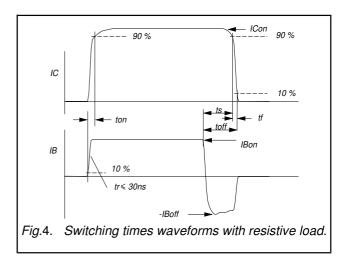
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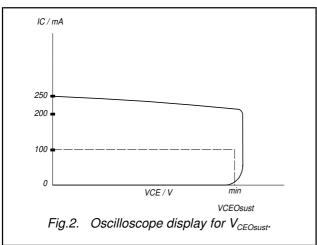
¹ Measured with half sine-wave voltage (curve tracer).

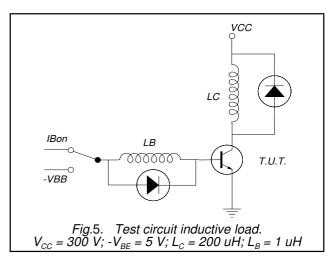
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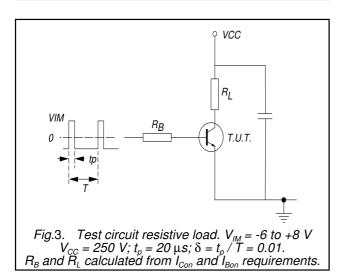
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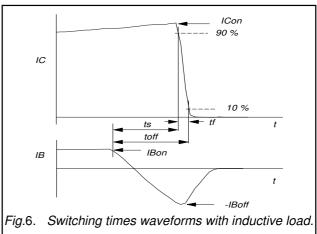






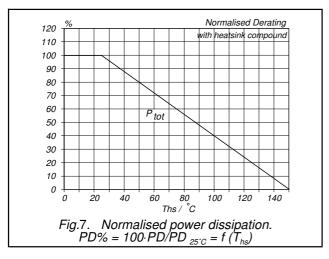


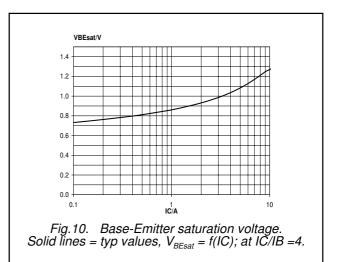


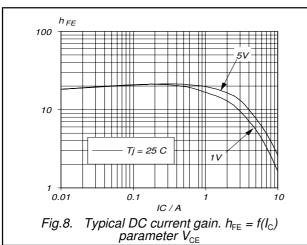


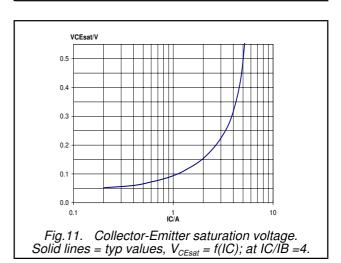
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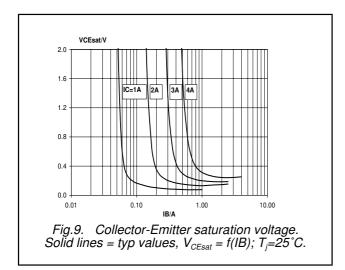
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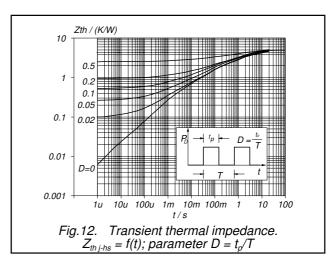






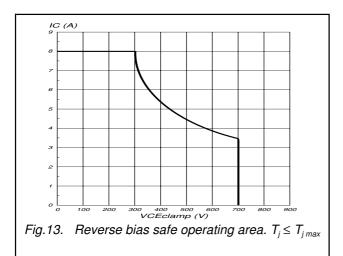


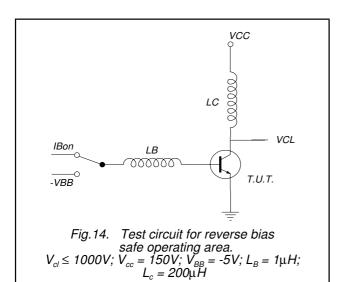


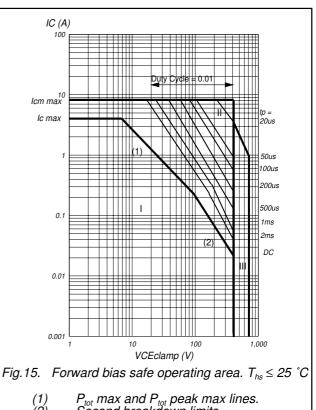


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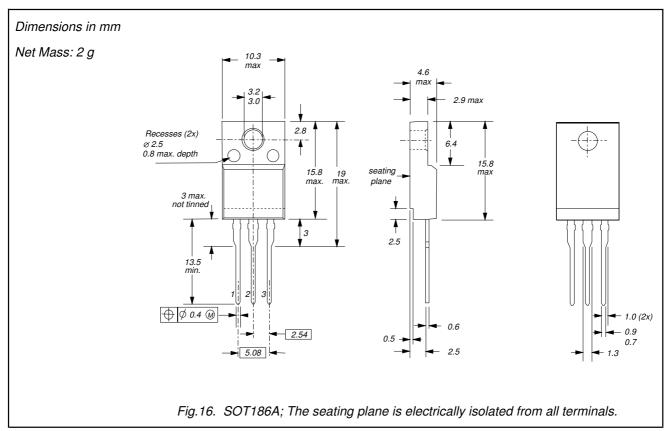
(1) P_{tot} max and P_{tot} peak max lines. (2) Second breakdown limits. I Region of permissible DC operation. II Extension for repetitive pulse operation. III Extension during turn-on in single transistor converters provided that $R_{BE} \leq 100 \ \Omega$ and $t_p \leq 0.6 \ \mu s$. NB: Mounted with heatsink compound and

NB: Mounted with heatsink compound and 30 ± 5 newton force on the centre of the envelope.

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MECHANICAL DATA



Notes

- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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